VS-E4PH3006L-N3

Vishay Semiconductors



Hyperfast Soft Recovery Diode, 30 A FRED Pt® Gen 4

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PRIMARY CHARACTERISTICS								
I _{F(AV)} 30 A								
V _R	600 V							
V _F at I _F	1.37 V							
t _{rr} typ.	see Recovery table							
T _J max.	175 °C							
Package	TO-247AD 2L							
Circuit configuration	Single							

FEATURES

- Gen 4 FRED Pt[®] technology
- Low I_{BBM} and reverse recovery charge
- · Very low forward voltage drop
- · Polymide passivated chip for high reliability standard
- 175 °C operating junction temperature
- Designed and gualified according to JEDEC[®]-JESD 47
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION

Gen 4 Fred technology, state of the art, ultrafast V_F, soft switching optimized for Discontinuous (Critical) Mode (DCM) and IGBT F/W diode.

The minimized conduction loss, optimized stored charge and low recovery current minimized the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS					
Cathode to anode voltage	V _R		600	V					
Average rectified current	I _{F(AV)}	T _C = 122 °C	30						
Single pulse forward current	I _{FSM}	T_C = 25 °C, t_p = 8.3 ms half sine wave	240	A					
Operating junction and storage temperatures	T _J , T _{Stg}		-55 to +175	°C					

ELECTRICAL SPECIFICATIONS ($T_J = 25$ °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Breakdown voltage, blocking voltage	V_{BR} , V_{R}	I _R = 100 μA	600	-	-				
Forward voltage		I _F = 30 A	-	1.65	2				
		I _F = 60 A	-	1.95	-]			
	N	I _F = 30 A, T _J = 125 °C	-	1.44	-	V			
	V _F	I _F = 60 A, T _J = 125 °C	-	1.78	-				
		I _F = 30 A, T _J = 150 °C	-	1.37	1.6				
		I _F = 60 A, T _J = 150 °C	-	1.68	-				
Bayaraa laakaga ayrrant		V _R = V _R rated	-	-	50				
Reverse leakage current	I _R	$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	-	500	μA			
Junction capacitance	CT	V _R = 600 V	-	18.3	-	pF			

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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST C	ONDITIONS	MIN.	TYP.	MAX.	UNITS		
Reverse recovery time	+	T _J = 25 °C		-	55	-	ns		
	t _{rr}	T _J = 125 °C	I _F = 30 A dI _F /dt = 1000 A/µs V _R = 400 V	-	75	-			
Real recovery ourrent	I _{RRM}	T _J = 25 °C		-	13	-	^		
Peak recovery current		T _J = 125 °C		-	23	-	A		
Powerea receivery charge	Q _{rr}	T _J = 25 °C		-	500	-			
Reverse recovery charge		T _J = 125 °C		-	1250	-	nC		

THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Thermal resistance, junction to case	R _{thJC}		-	-	1				
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	40	°C/W			
Thermal resistance, case to heat sink	hermal resistance, case to heat sink R _{thCS} Mounting surface, flat, smooth and greased		-	0.4	-				
Weight			-	6.0	-	g			
Weight			-	0.21	-	oz.			
Mounting torque			6.0 (5)	-	12 (20)	kgf · cm (lbf · in)			
Marking device		Case style TO-247AD 2L	E4PH3006L						

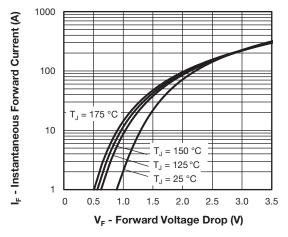


Fig. 1 - Typical Forward Voltage Drop Characteristics

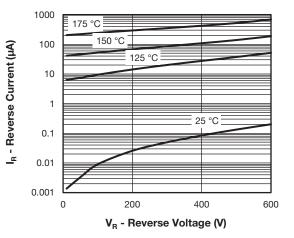


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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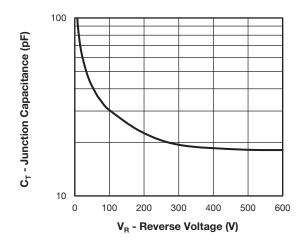


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

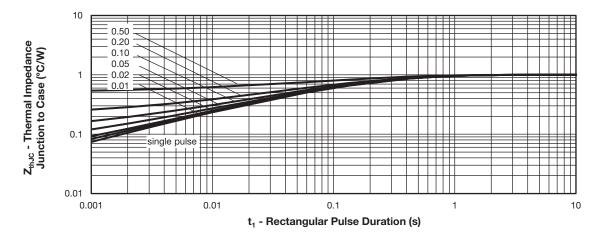
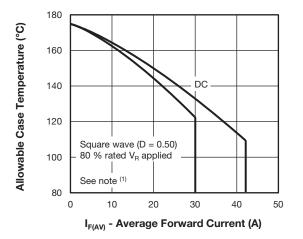
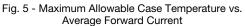


Fig. 4 - Max. Thermal Impedance Z_{thJC} Characteristics



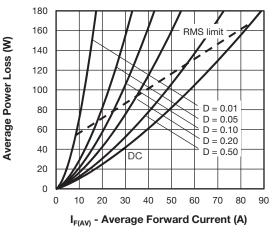
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Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;

Pd = forward power loss = $I_{F(AV)} \times V_{FM}$ at ($I_{F(AV)}/D$) (see fig. 5); Pd_{REV} = inverse power loss = $V_{R1} \times I_R$ (1 - D); I_R at V_{R1} = rated V_R





 $Pd_{REV} = inverse power loss = V_{R1} \times I_R (1 - 1)$

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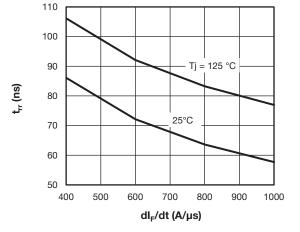


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

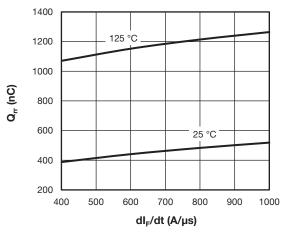


Fig. 8 - Typical Stored Charge vs. dl_F/dt

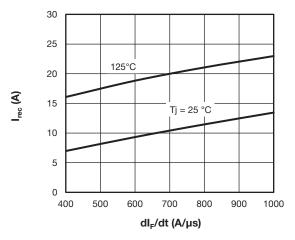
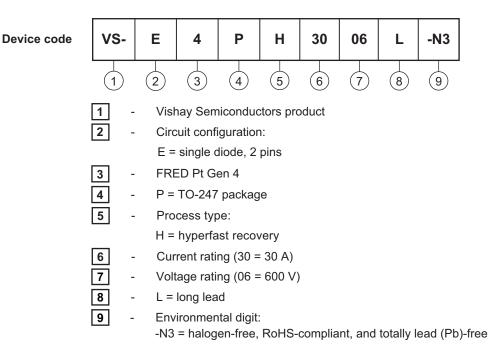


Fig. 9 - Typical Reverse Current vs. dl_F/dt

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ORDERING INFORMATION TABLE



ORDERING INFORMATION (Example)									
PREFERRED P/N	/N QUANTITY PER TUBE MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION								
VS-E4PH3006L-N3	25	500	Antistatic plastic tube						

LINKS TO RELATED DOCUMENTS						
Dimensions www.vishay.com/doc?95536						
Part marking information	www.vishay.com/doc?95648					



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TO-247AD 2L

DIMENSIONS in millimeters and inches



Section C - C, D - D

(b. b2)

(4)

/	\square
	C C
Vie	<u>w B</u>

SYMBOL	MILLIMETERS		INCHES		NOTES	SYMBOL	MILLIMETERS		INCHES		NOTES	
STIVIDUL	MIN.	MAX.	MIN.	MAX.	NOTES		STIVIDUL	MIN.	MAX.	MIN.	MAX.	NUTES
А	4.65	5.31	0.183	0.209			Е	15.29	15.87	0.602	0.625	3
A1	2.21	2.59	0.087	0.102			E1	13.46	-	0.53	-	
A2	1.50	2.49	0.059	0.098			е	5.46	BSC	0.215	BSC	
b	0.99	1.40	0.039	0.055			ØК	0.2	254	0.0)10	
b1	0.99	1.35	0.039	0.053			L	19.81	20.32	0.780	0.800	
b2	1.65	2.39	0.065	0.094			L1	3.71	4.29	0.146	0.169	
b3	1.65	2.34	0.065	0.092			ØР	3.56	3.66	0.14	0.144	
С	0.38	0.89	0.015	0.035			Ø P1	-	6.98	-	0.275	
c1	0.38	0.84	0.015	0.033			Q	5.31	5.69	0.209	0.224	
D	19.71	20.70	0.776	0.815	3		R	4.52	5.49	0.178	0.216	
D1	13.08	-	0.515	-	4		S	5.51	BSC	0.217	BSC	
D2	0.51	1.35	0.020	0.053								

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5M-1994

⁽²⁾ Contour of slot optional

(3) Dimension D and E do not include mold flash. These dimensions are measured at the outermost extremes of the plastic body

(4) Thermal pad contour optional with dimensions D1 and E1

(5) Lead finish uncontrolled in L1

⁽⁶⁾ Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")

(7) Outline conforms to JEDEC® outline TO-247 with exception of dimension A min., D, E min., Q min., S, and note 4

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